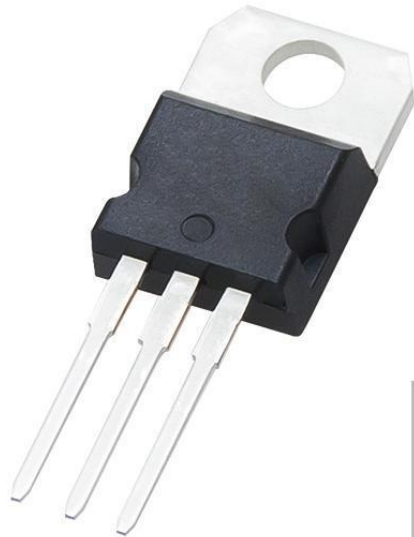




TR BD902;SGS;TO220;tranzystor PNP;Darl.;8A;100V;70W



Dane techniczne:

Nazwa: BD902

Układ Darlingtona

Typ tranzystora: bipolarny

Kierunek przewodnictwa: PNP

Prąd kolektora: 8A

Napięcie kolektor-emiter: 100V

Moc: 70W

Montaż: przewlekany(THT)

Obudowa: TO220

Producent: SGS

Silicon PNP Power Transistors

BD896/898/900/902

DESCRIPTION

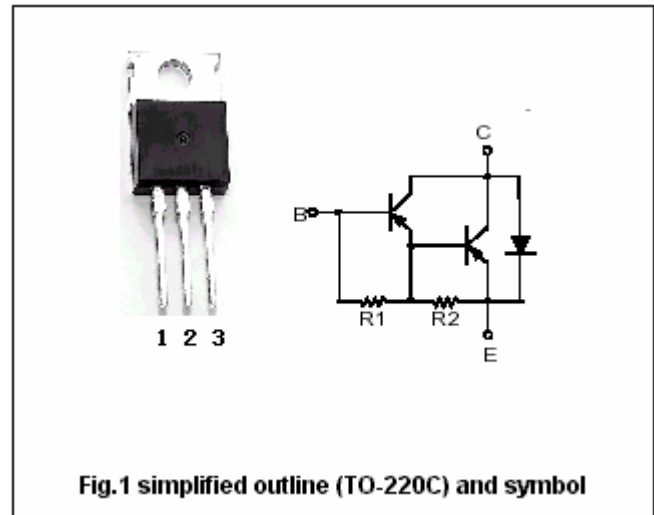
- With TO-220C package
- Complement to type BD895/897/899/901
- DARLINGTON

APPLICATIONS

- For use in output stages in audio equipment, general amplifier, and analogue switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	BD896	-45	V
		BD898	-60	
		BD900	-80	
		BD902	-100	
V_{CEO}	Collector-emitter voltage	BD896	-45	V
		BD898	-60	
		BD900	-80	
		BD902	-100	
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current-DC		-8	A
I_B	Base current		-300	mA
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	70	W
		$T_a=25^\circ\text{C}$	2	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

Silicon PNP Power Transistors

BD896/898/900/902

CHARACTERISTICS

T_j=25°C unless otherwise specified

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SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	BD896	I _C =-100mA, I _B =0	-45			V
		BD898		-60			
		BD900		-80			
		BD902		-100			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-3A, I _B =-12mA			-2.5	V
V _{BE}	Base-emitter on voltage		I _C =-3A; V _{CE} =-3V			-2.5	V
I _{CBO}	Collector cut-off current	BD896	V _{CB} =-45V, I _E =0 T _C =100°C			-0.2 -2.0	mA
		BD898	V _{CB} =-60V, I _E =0 T _C =100°C			-0.2 -2.0	
		BD900	V _{CB} =-80V, I _E =0 T _C =100°C			-0.2 -2.0	
		BD902	V _{CB} =-100V, I _E =0 T _C =100°C			-0.2 -2.0	
I _{CEO}	Collector cut-off current	BD896	V _{CE} =-30V, I _B =0			-0.5	mA
		BD898	V _{CE} =-30V, I _B =0				
		BD900	V _{CE} =-40V, I _B =0				
		BD902	V _{CE} =-50V, I _B =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-2	mA
h _{FE}	DC current gain		I _C =-3A; V _{CE} =-3V	750			
V _{EC}	Diode forward voltage		I _E =-8A			-3.5	V
ton	Turn-on time		I _C =-3A; I _{B1} =-I _{B2} =-12mA V _{BE} =3.5V; R _L =10Ω; t _p =20μs		1		μs
toff	Turn-off time				5		μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{thj-c}	Thermal resistance junction to case	1.79	°C/W

PACKAGE OUTLINE

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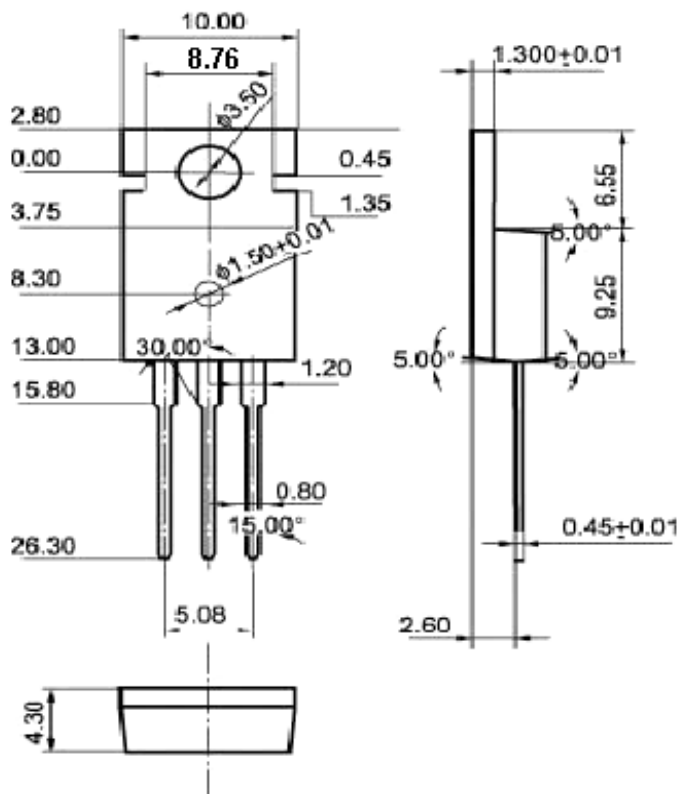


Fig.2 Outline dimensions